

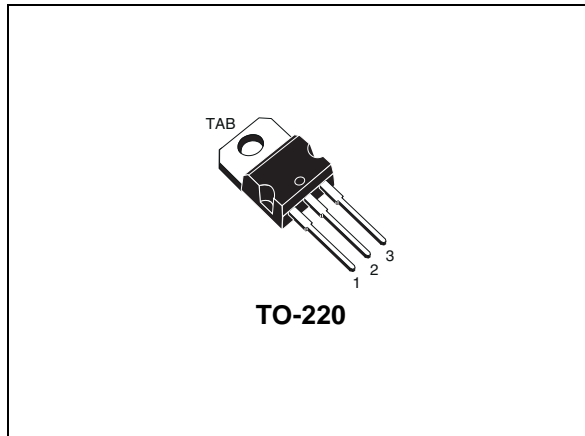
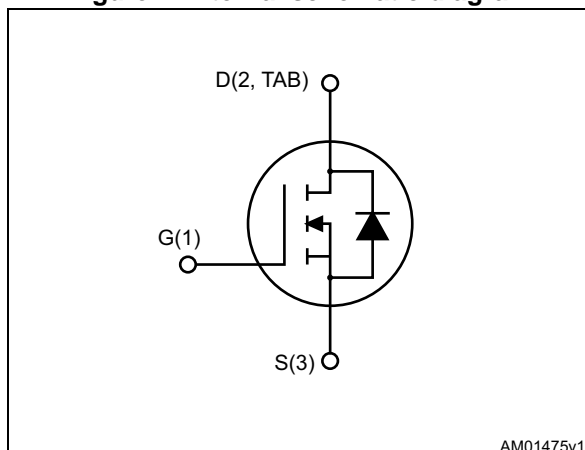


**THE DATASHEET OF
STP170N8F7**



N-channel 80 V, 0.003 Ω typ., 120 A, STripFET™ F7 Power MOSFET in TO-220 package

Datasheet — production data


Figure 1. Internal schematic diagram


Features

Order code	V_{DS}	$R_{DS(on)}$ max.	I_D	P_{TOT}
STP170N8F7	80 V	0.0039 Ω	120 A	250 W

- Among the lowest $R_{DS(on)}$ on the market
- Excellent figure of merit (FoM)
- Low C_{rSS}/C_{iSS} ratio for EMI immunity
- High avalanche ruggedness

Applications

- Switching applications

Description

This N-channel Power MOSFET utilizes STripFET™ F7 technology with an enhanced trench gate structure that results in very low on-state resistance, while also reducing internal capacitance and gate charge for faster and more efficient switching.

Table 1. Device summary

Order code	Marking	Package	Packaging
STP170N8F7	170N8F7	TO-220	Tube

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1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source voltage	80	V
V_{GS}	Gate-source voltage	± 20	V
$I_D^{(1)}$	Drain current (continuous)	120	A
$I_D^{(1)}$	Drain current (continuous) at $T_C = 100\text{ }^\circ\text{C}$	120	A
I_{DM}	Drain current (pulsed)	480	A
$P_{TOT}^{(1)}$	Total dissipation at $T_C = 25\text{ }^\circ\text{C}$	250	W
T_J	Operating junction temperature	-55 to 175	$^\circ\text{C}$
T_{stg}	Storage temperature		$^\circ\text{C}$

1. Limited by package and rated according to R_{thj-c} .

Table 3. Thermal resistance

Symbol	Parameter	Value	Unit
$R_{thj-case}$	Thermal resistance junction-case	0.6	$^\circ\text{C/W}$
$R_{thj-amb}$	Thermal resistance junction-ambient max.	62.5	$^\circ\text{C/W}$

Table 4. Avalanche data

Symbol	Parameter	Value	Unit
I_{AV}	Not-repetitive avalanche current, (pulse width limited by T_{jmax})	35	A
E_{AS}	Single pulse avalanche energy (starting $T_J = 25\text{ }^\circ\text{C}$, $I_D = I_{AV}$, $V_{DD} = 50\text{ V}$)	615	mJ

2 Electrical characteristics

(T_{CASE} = 25 °C unless otherwise specified)

Table 5. On/off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
V _{(BR)DSS}	Drain-source breakdown voltage	V _{GS} = 0, I _D = 250 μA	80			V
I _{DSS}	Zero gate voltage drain current	V _{GS} = 0, V _{DS} = 80 V			1	μA
		V _{GS} = 0, V _{DS} = 80 V, T _C = 125 °C			100	μA
I _{GSS}	Gate body leakage current	V _{DS} = 0, V _{GS} = +20 V			100	nA
V _{GS(th)}	Gate threshold voltage	V _{DS} = V _{GS} , I _D = 250 μA	2.5		4.5	V
R _{DS(on)}	Static drain-source on- resistance	V _{GS} = 10 V, I _D = 60 A		0.003	0.0039	Ω

Table 6. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C _{iSS}	Input capacitance	V _{GS} = 0, V _{DS} = 40 V, f = 1 MHz	-	8710	-	pF
C _{oSS}	Output capacitance		-	1330	-	pF
C _{rSS}	Reverse transfer capacitance		-	78	-	pF
Q _g	Total gate charge	V _{DD} = 40 V, I _D = 120 A	-	120	-	nC
Q _{gs}	Gate-source charge	V _{GS} = 10 V	-	43	-	nC
Q _{gd}	Gate-drain charge	Figure 14	-	26	-	nC

Table 7. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
t _{d(on)}	Turn-on delay time	V _{DD} = 40 V, I _D = 60 A, R _G = 4.7 Ω, V _{GS} = 10 V Figure 13	-	38	-	ns
t _r	Rise time		-	53	-	ns
t _{d(off)}	Turn-off delay time		-	79	-	ns
t _f	Fall time		-	37	-	ns

Table 8. Source-drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain current		-		120	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)		-		480	A
$V_{SD}^{(2)}$	Forward on voltage	$V_{GS}=0, I_{SD} = 120 \text{ A}$	-		1.2	V
t_{rr}	Reverse recovery time	$I_{SD} = 120 \text{ A},$ $di/dt = 100 \text{ A}/\mu\text{s},$ $V_{DD} = 64 \text{ V}, T_j = 150 \text{ }^\circ\text{C}$	-	54		ns
Q_{rr}	Reverse recovery charge		-	78		nC
I_{RRM}	Reverse recovery current		-	2.9		A

1. Pulse width limited by safe operating area.
2. Pulsed: pulse duration=300 μs , duty cycle 1.5%.

2.1 Electrical characteristics (curves)

Figure 2. Safe operating area

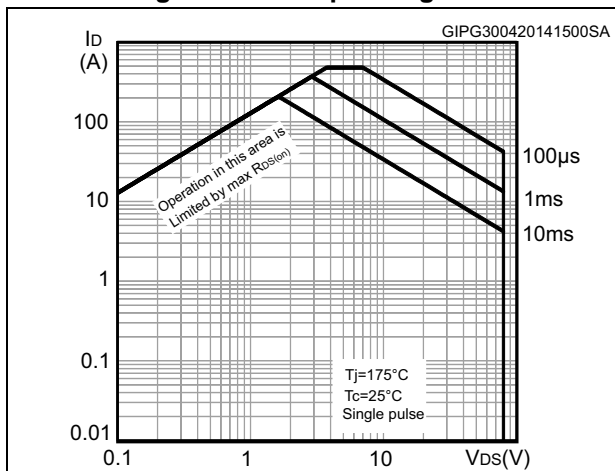


Figure 3. Thermal impedance

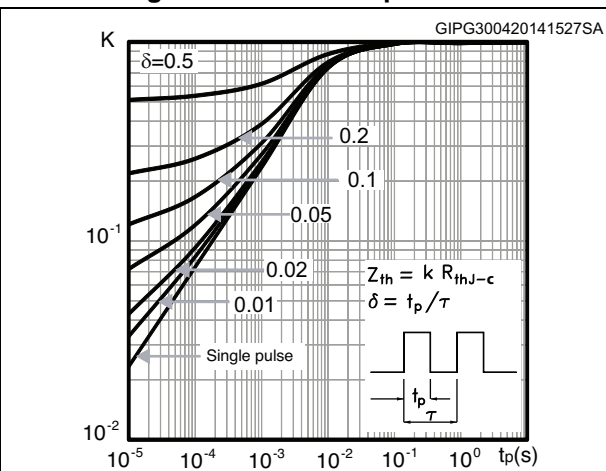


Figure 4. Output characteristics

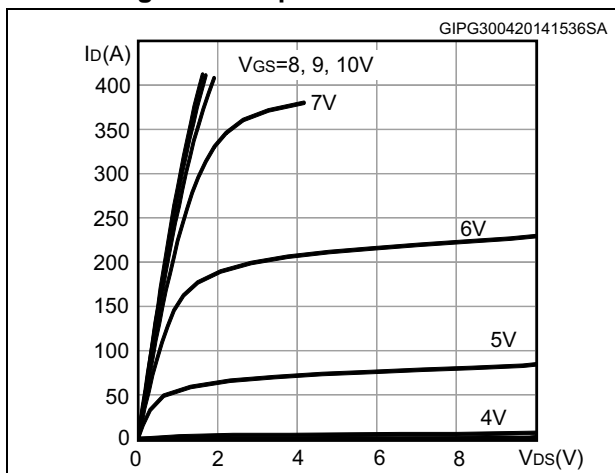


Figure 5. Transfer characteristics

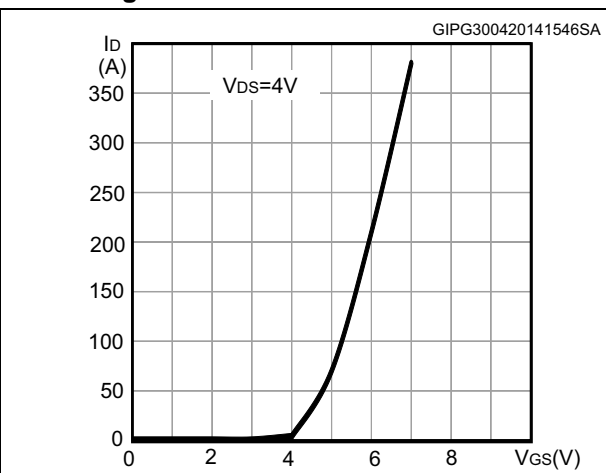


Figure 6. Gate charge vs gate-source voltage

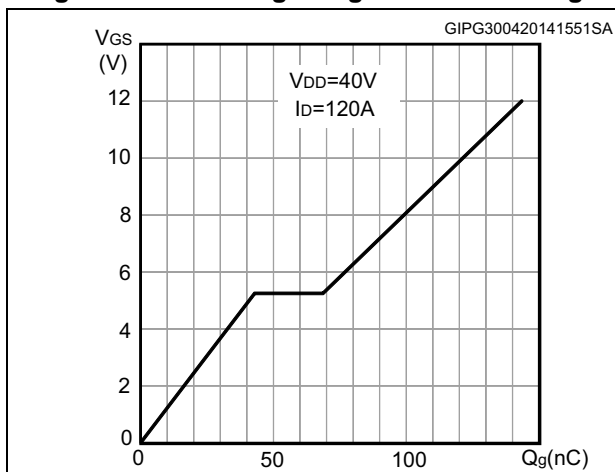


Figure 7. Static drain-source on-resistance

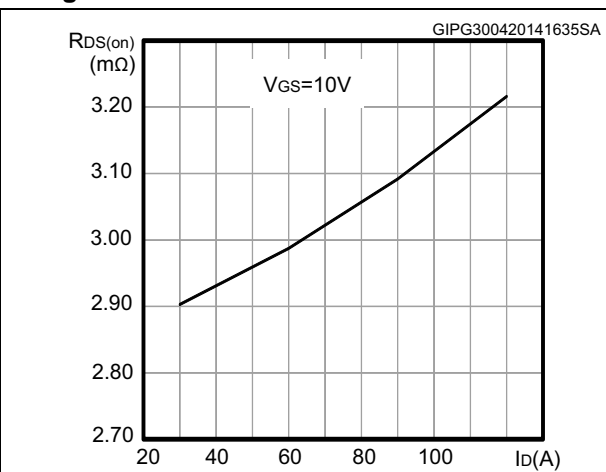


Figure 8. Capacitance variations

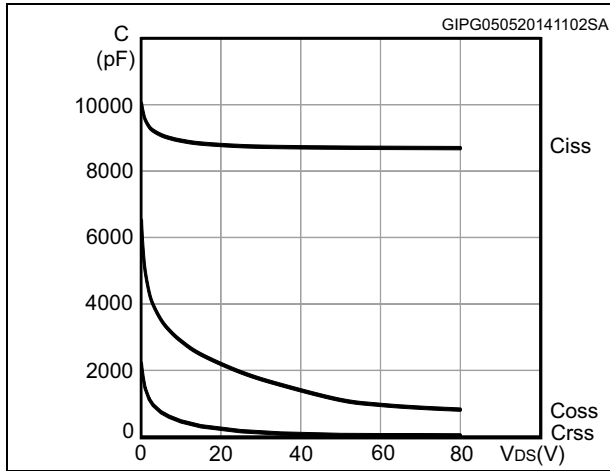


Figure 9. Normalized gate threshold voltage vs temperature

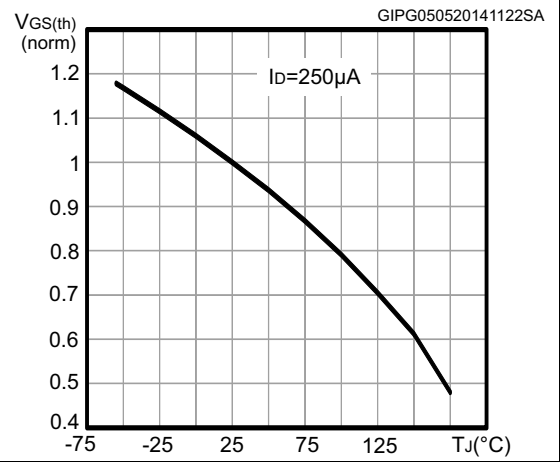


Figure 10. Normalized on-resistance vs temperature

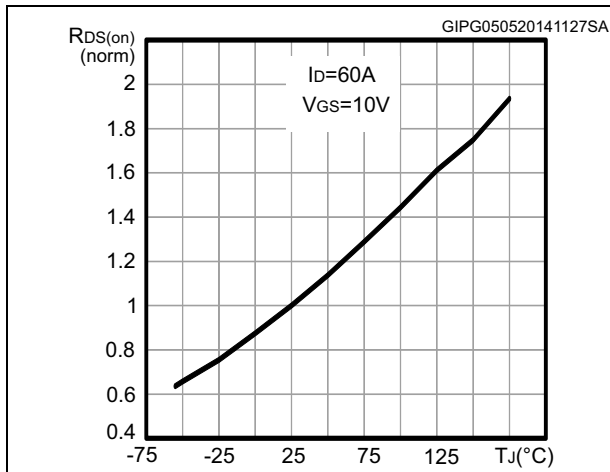


Figure 11. Normalized V_{(BR)DSS} vs temperature

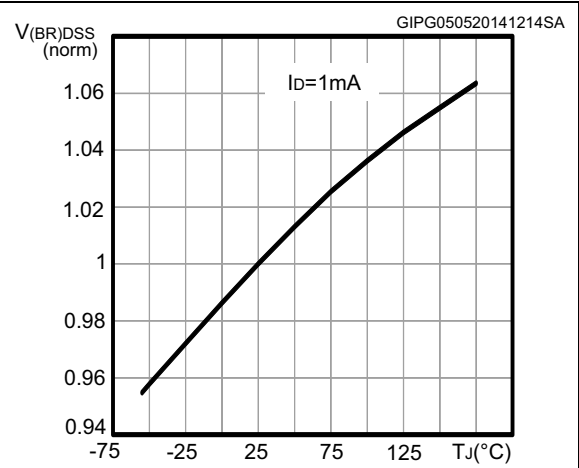
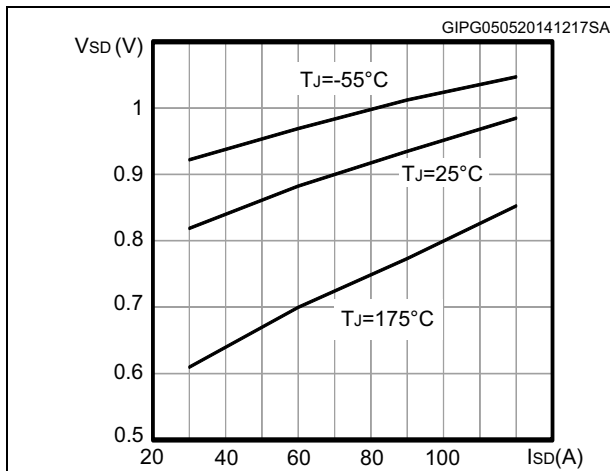


Figure 12. Source-drain diode forward characteristics



3 Test circuits

Figure 13. Switching times test circuit for resistive load

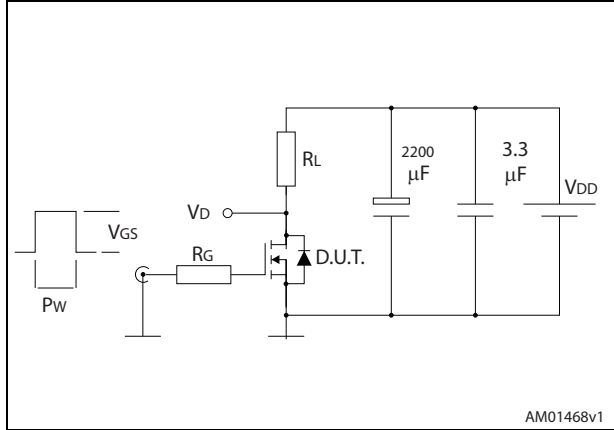


Figure 14. Gate charge test circuit

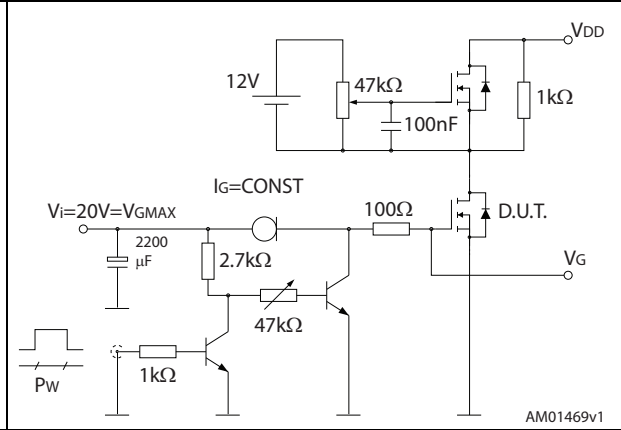


Figure 15. Test circuit for inductive load switching and diode recovery times

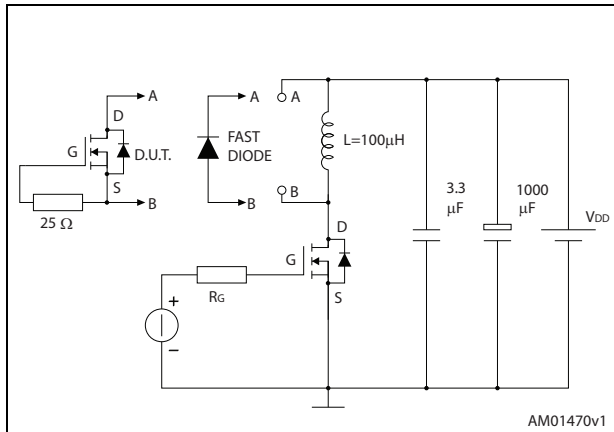


Figure 16. Unclamped inductive load test circuit

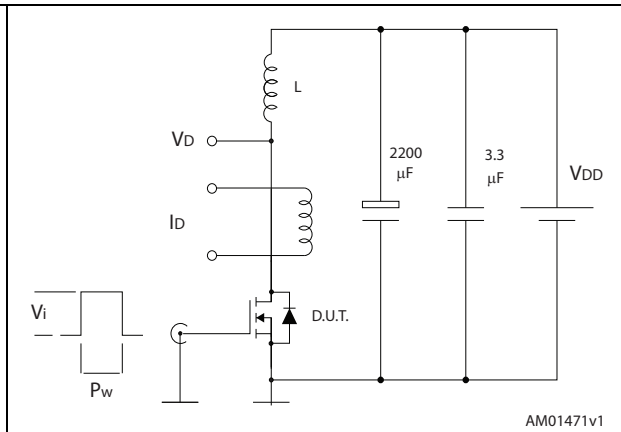


Figure 17. Unclamped inductive waveform

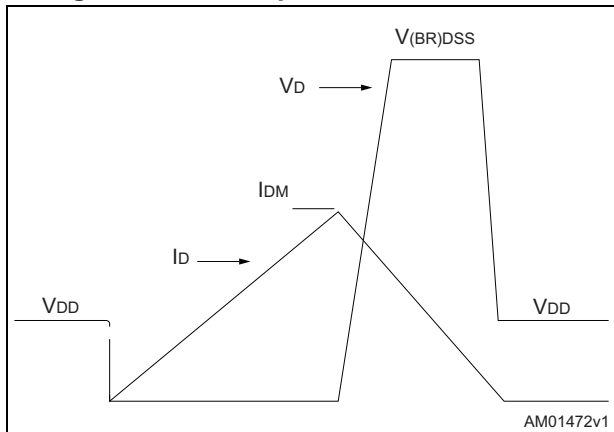
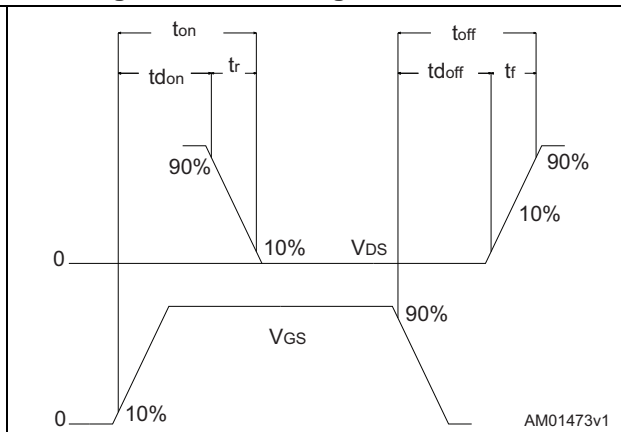


Figure 18. Switching time waveform



4 Package mechanical data

Figure 19. TO-220 type A drawing

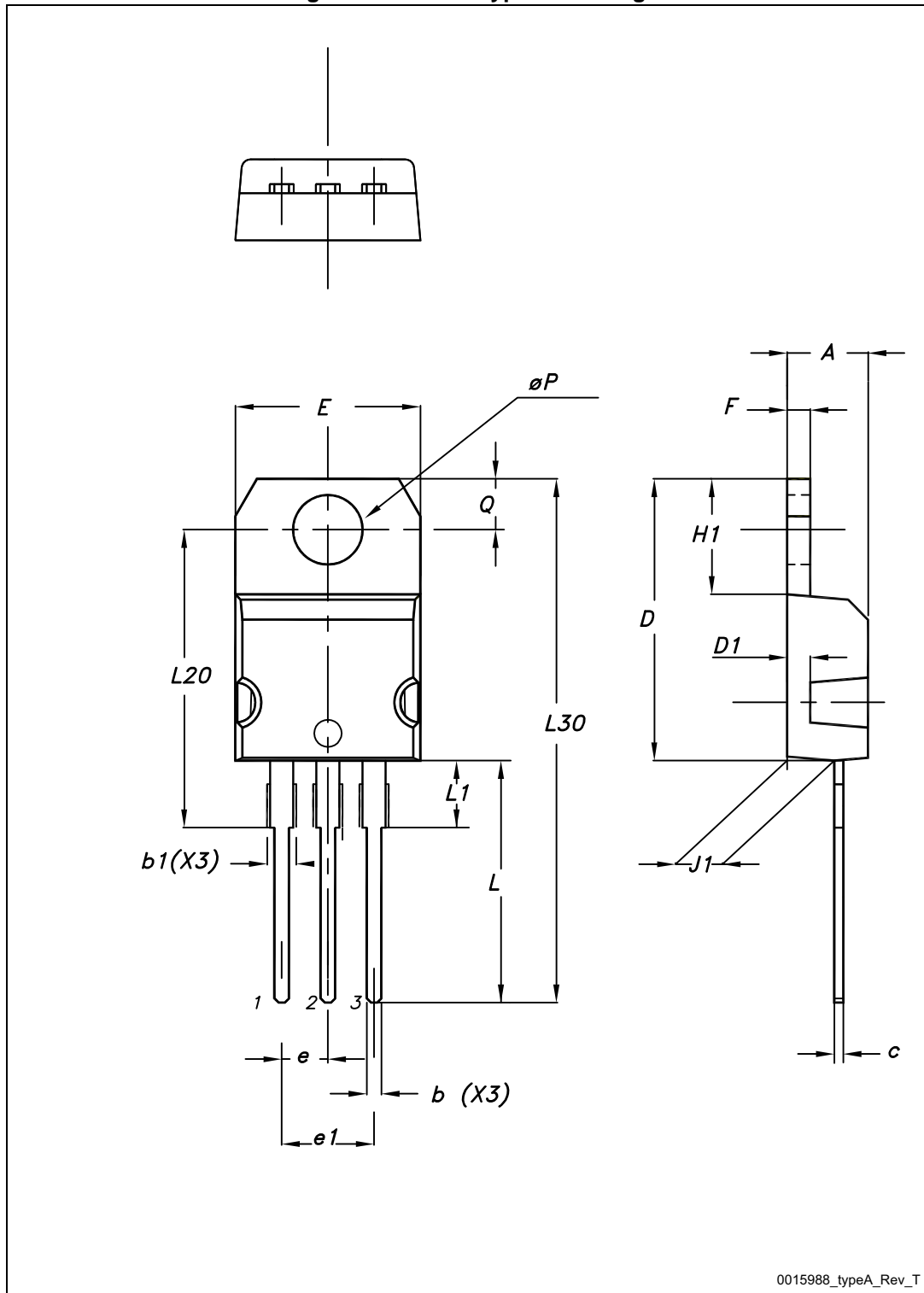


Table 9. TO-220 type A mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.40		4.60
b	0.61		0.88
b1	1.14		1.70
c	0.48		0.70
D	15.25		15.75
D1		1.27	
E	10		10.40
e	2.40		2.70
e1	4.95		5.15
F	1.23		1.32
H1	6.20		6.60
J1	2.40		2.72
L	13		14
L1	3.50		3.93
L20		16.40	
L30		28.90	
ØP	3.75		3.85
Q	2.65		2.95

5 Revision history

Table 10. Document revision history

Date	Revision	Changes
16-Apr-2013	1	First release.
15-May-2014	2	<ul style="list-style-type: none"> – The part number STH170N8F7-2 has been moved to a separate datasheet – Modified: $R_{DS(on)}$ in cover page – Modified: Figure 1 – Modified: I_D ($T_C = 100\text{ °C}$), P_{TOT} and E_{AS} values in Table 2 – Modified: $R_{thj-case}$ value in Table 3 – Added: Table 4 – Modified: I_{DSS}, $V_{GS(th)}$ and $R_{DS(on)}$ values in Table 5 – Modified: the entire typical values in table Table 6, 7 and 8 – Added: Section 2.1: Electrical characteristics (curves) – Updated: Section Figure 19.: TO-220 type A drawing – Minor text changes
20-Feb-2015	3	– Updated title, features and description in cover page.

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